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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	540
Number of Logic Elements/Cells	4320
Total RAM Bits	94208
Number of I/O	278
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmx02-4000he-5fg484i

The logic blocks, Programmable Functional Unit (PFU) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each row has either the logic blocks or the EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the MachXO2 family, the number of sysIO banks varies by device. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks; these blocks are found in MachXO2-640/U and larger devices. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag “hard” control logic to minimize LUT usage.

The MachXO2 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and device is configured, the device enters into user mode with these registers SET/RESET according to the configuration setting, allowing device entering to a known state for predictable system function.

The MachXO2 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks on MachXO2-640U, MachXO2-1200/U and larger devices. These blocks are located at the ends of the on-chip Flash block. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

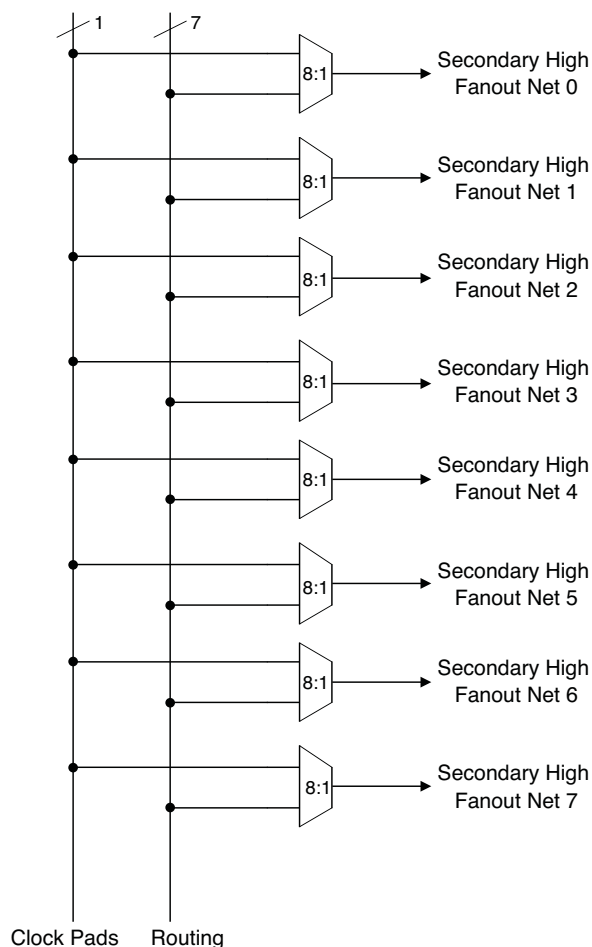
MachXO2 devices provide commonly used hardened functions such as SPI controller, I²C controller and timer/counter. MachXO2-640/U and higher density devices also provide User Flash Memory (UFM). These hardened functions and the UFM interface to the core logic and routing through a WISHBONE interface. The UFM can also be accessed through the SPI, I²C and JTAG ports.

Every device in the family has a JTAG port that supports programming and configuration of the device as well as access to the user logic. The MachXO2 devices are available for operation from 3.3 V, 2.5 V and 1.2 V power supplies, providing easy integration into the overall system.

PFU Blocks

The core of the MachXO2 device consists of PFU blocks, which can be programmed to perform logic, arithmetic, distributed RAM and distributed ROM functions. Each PFU block consists of four interconnected slices numbered 0 to 3 as shown in Figure 2-3. Each slice contains two LUTs and two registers. There are 53 inputs and 25 outputs associated with each PFU block.

Figure 2-6. Secondary High Fanout Nets for MachXO2 Devices



sysCLOCK Phase Locked Loops (PLLs)

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. The MachXO2-640U, MachXO2-1200/U and larger devices have one or more sysCLOCK PLL. CLKI is the reference frequency input to the PLL and its source can come from an external I/O pin or from internal routing. CLKFB is the feedback signal to the PLL which can come from internal routing or an external I/O pin. The feedback divider is used to multiply the reference frequency and thus synthesize a higher frequency clock output.

The MachXO2 sysCLOCK PLLs support high resolution (16-bit) fractional-N synthesis. Fractional-N frequency synthesis allows the user to generate an output clock which is a non-integer multiple of the input frequency. For more information about using the PLL with Fractional-N synthesis, please see TN1199, [MachXO2 sysCLOCK PLL Design and Usage Guide](#).

Each output has its own output divider, thus allowing the PLL to generate different frequencies for each output. The output dividers can have a value from 1 to 128. The output dividers may also be cascaded together to generate low frequency clocks. The CLKOP, CLKOS, CLKOS2, and CLKOS3 outputs can all be used to drive the MachXO2 clock distribution network directly or general purpose routing resources can be used.

The LOCK signal is asserted when the PLL determines it has achieved lock and de-asserted if a loss of lock is detected. A block diagram of the PLL is shown in Figure 2-7.

The setup and hold times of the device can be improved by programming a phase shift into the CLKOS, CLKOS2, and CLKOS3 output clocks which will advance or delay the output clock with reference to the CLKOP output clock.

More information on the input gearbox is available in TN1203, [Implementing High-Speed Interfaces with MachXO2 Devices](#).

Output Gearbox

Each PIC on the top edge has a built-in 8:1 output gearbox. Each of these output gearboxes may be programmed as a 7:1 serializer or as one ODDR4 (8:1) gearbox or as two ODDR2 (4:1) gearboxes. Table 2-10 shows the gearbox signals.

Table 2-10. Output Gearbox Signal List

Name	I/O Type	Description
Q	Output	High-speed data output
D[7:0]	Input	Low-speed data from device core
Video TX(7:1): D[6:0]		
GDDR4(8:1): D[7:0]		
GDDR2(4:1)(IOL-A): D[3:0]		
GDDR2(4:1)(IOL-C): D[7:4]		
SCLK	Input	Slow-speed system clock
ECLK [1:0]	Input	High-speed edge clock
RST	Input	Reset

The gearboxes have three stage pipeline registers. The first stage registers sample the low-speed input data on the low-speed system clock. The second stage registers transfer data from the low-speed clock registers to the high-speed clock registers. The third stage pipeline registers controlled by high-speed edge clock shift and mux the high-speed data out to the sysIO buffer. Figure 2-17 shows the output gearbox block diagram.

Figure 2-21. I²C Core Block Diagram

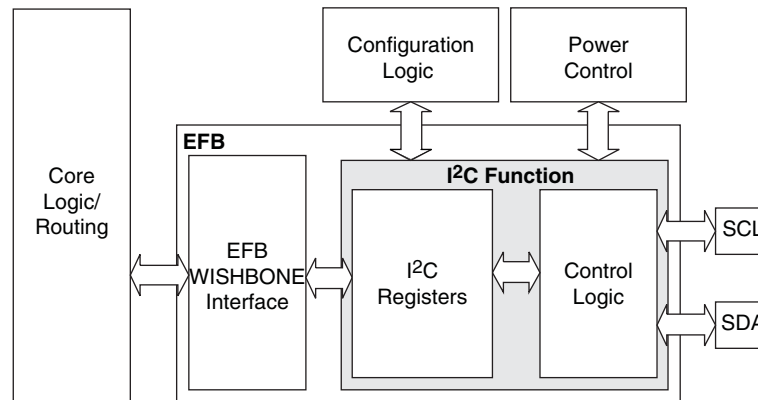


Table 2-15 describes the signals interfacing with the I²C cores.

Table 2-15. I²C Core Signal Description

Signal Name	I/O	Description
i2c_scl	Bi-directional	Bi-directional clock line of the I ² C core. The signal is an output if the I ² C core is in master mode. The signal is an input if the I ² C core is in slave mode. MUST be routed directly to the pre-assigned I/O of the chip. Refer to the Pinout Information section of this document for detailed pad and pin locations of I ² C ports in each MachXO2 device.
i2c_sda	Bi-directional	Bi-directional data line of the I ² C core. The signal is an output when data is transmitted from the I ² C core. The signal is an input when data is received into the I ² C core. MUST be routed directly to the pre-assigned I/O of the chip. Refer to the Pinout Information section of this document for detailed pad and pin locations of I ² C ports in each MachXO2 device.
i2c_irqo	Output	Interrupt request output signal of the I ² C core. The intended usage of this signal is for it to be connected to the WISHBONE master controller (i.e. a microcontroller or state machine) and request an interrupt when a specific condition is met. These conditions are described with the I ² C register definitions.
cfg_wake	Output	Wake-up signal – To be connected only to the power module of the MachXO2 device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, I ² C Tab.
cfg_stdbby	Output	Stand-by signal – To be connected only to the power module of the MachXO2 device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, I ² C Tab.

Hardened SPI IP Core

Every MachXO2 device has a hard SPI IP core that can be configured as a SPI master or slave. When the IP core is configured as a master it will be able to control other SPI enabled chips connected to the SPI bus. When the core is configured as the slave, the device will be able to interface to an external SPI master. The SPI IP core on MachXO2 devices supports the following functions:

- Configurable Master and Slave modes
- Full-Duplex data transfer
- Mode fault error flag with CPU interrupt capability
- Double-buffered data register
- Serial clock with programmable polarity and phase
- LSB First or MSB First Data Transfer
- Interface to custom logic through 8-bit WISHBONE interface

For more details on these embedded functions, please refer to TN1205, [Using User Flash Memory and Hardened Control Functions in MachXO2 Devices](#).

User Flash Memory (UFM)

MachXO2-640/U and higher density devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I²C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1205, [Using User Flash Memory and Hardened Control Functions in MachXO2 Devices](#).

Standby Mode and Power Saving Options

MachXO2 devices are available in three options for maximum flexibility: ZE, HC and HE devices. The ZE devices have ultra low static and dynamic power consumption. These devices use a 1.2 V core voltage that further reduces power consumption. The HC and HE devices are designed to provide high performance. The HC devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the HE devices operate at 1.2 V V_{CC} .

MachXO2 devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO2 devices support an ultra low power Stand-by mode. While most of these features are available in all three device types, these features are mainly intended for use with MachXO2 ZE devices to manage power consumption.

In the stand-by mode the MachXO2 devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I²C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO2 devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

Table 2-18. MachXO2 Power Saving Features Description

Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, analog circuitry such as the POR, PLLs, on-chip oscillator, and referenced and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors V _{CC} levels. In the event of unsafe V _{CC} drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Referenced and differential I/O buffers (used to implement standards such as HSTL, SSTL and LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1198, [Power Estimation and Management for MachXO2 Devices](#).

Power On Reset

MachXO2 devices have power-on reset circuitry to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CCINT} and V_{CCIO0} (controls configuration) voltage levels. It then triggers download from the on-chip configuration Flash memory after reaching the V_{PORUP} level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For devices without voltage regulators (ZE and HE devices), V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators (HC devices), V_{CCINT} is regulated from the V_{CC} supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as Flash Download Time (t_{REFRESH}) in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration. Note that for HC devices, a separate POR circuit monitors external V_{CC} voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor V_{CCINT} levels. If V_{CCINT} drops below V_{PORDNBG} level (with the bandgap circuitry switched on) or below V_{PORDNSRAM} level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the V_{CCINT} and V_{CCIO} voltage levels. V_{PORDNBG} and V_{PORDNSRAM} are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once a ZE or HE device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a minimal, low power POR circuit is still operational (this corresponds to the V_{PORDNSRAM} reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the V_{CC} supply dropping below V_{CC} (min) they should not shut down the bandgap or POR circuit.

Power-On-Reset Voltage Levels^{1, 2, 3, 4, 5}

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for HC devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Programming/Erase Specifications

Symbol	Parameter	Min.	Max. ¹	Units
N_{PROG}	Flash Programming cycles per $t_{RETENTION}$	—	10,000	Cycles
	Flash functional programming cycles	—	100,000	
$t_{RETENTION}$	Data retention at 100 °C junction temperature	10	—	Years
	Data retention at 85 °C junction temperature	20	—	

1. Maximum Flash memory reads are limited to 7.5E13 cycles over the lifetime of the product.

Hot Socketing Specifications^{1, 2, 3}

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	μA

1. Insensitive to sequence of V_{CC} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO} .
2. $0 < V_{CC} < V_{CC} (MAX)$, $0 < V_{CCIO} < V_{CCIO} (MAX)$.
3. I_{DK} is additive to I_{PU} , I_{PD} or I_{BH} .

ESD Performance

Please refer to the [MachXO2 Product Family Qualification Summary](#) for complete qualification data, including ESD performance.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$I_{IL}, I_{IH}^{1,4}$	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH} (MAX)$	—	—	+175	μA
		Clamp OFF and $V_{IN} = V_{CCIO}$	-10	—	10	μA
		Clamp OFF and $V_{CCIO} - 0.97 V < V_{IN} < V_{CCIO}$	-175	—	—	μA
		Clamp OFF and $0 V < V_{IN} < V_{CCIO} - 0.97 V$	—	—	10	μA
		Clamp OFF and $V_{IN} = GND$	—	—	10	μA
		Clamp ON and $0 V < V_{IN} < V_{CCIO}$	—	—	10	μA
I_{PU}	I/O Active Pull-up Current	$0 < V_{IN} < 0.7 V_{CCIO}$	-30	—	-309	μA
I_{PD}	I/O Active Pull-down Current	$V_{IL} (MAX) < V_{IN} < V_{CCIO}$	30	—	305	μA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL} (MAX)$	30	—	—	μA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7 V_{CCIO}$	-30	—	—	μA
I_{BHLO}	Bus Hold Low Overdrive current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	305	μA
I_{BHHO}	Bus Hold High Overdrive current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	-309	μA
V_{BHT}^3	Bus Hold Trip Points		$V_{IL} (MAX)$	—	$V_{IH} (MIN)$	V
C1	I/O Capacitance ²	$V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 \text{ to } V_{IH} (MAX)$	3	5	9	pF
C2	Dedicated Input Capacitance ²	$V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 \text{ to } V_{IH} (MAX)$	3	5.5	7	pF
V_{HYST}	Hysteresis for Schmitt Trigger Inputs ⁵	$V_{CCIO} = 3.3 V, \text{Hysteresis} = \text{Large}$	—	450	—	mV
		$V_{CCIO} = 2.5 V, \text{Hysteresis} = \text{Large}$	—	250	—	mV
		$V_{CCIO} = 1.8 V, \text{Hysteresis} = \text{Large}$	—	125	—	mV
		$V_{CCIO} = 1.5 V, \text{Hysteresis} = \text{Large}$	—	100	—	mV
		$V_{CCIO} = 3.3 V, \text{Hysteresis} = \text{Small}$	—	250	—	mV
		$V_{CCIO} = 2.5 V, \text{Hysteresis} = \text{Small}$	—	150	—	mV
		$V_{CCIO} = 1.8 V, \text{Hysteresis} = \text{Small}$	—	60	—	mV
		$V_{CCIO} = 1.5 V, \text{Hysteresis} = \text{Small}$	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. $T_A = 25^\circ C, f = 1.0 \text{ MHz}$.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO} , a transient current typically of 30 ns in duration or less with a peak current of 6 mA can occur on the high-to-low transition. For true LVDS output pins in MachXO2-640U, MachXO2-1200/U and larger devices, V_{IH} must be less than or equal to V_{CCIO} .
5. With bus keeper circuit turned on. For more details, refer to TN1202, [MachXO2 sysIO Usage Guide](#).

sysIO Single-Ended DC Electrical Characteristics^{1, 2}

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max. ⁴ (mA)	I_{OH} Max. ⁴ (mA)
	Min. (V) ³	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
							16	-16
							24	-24
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
							16	-16
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.8	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.5	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
					0.2	$V_{CCIO} - 0.2$	8	-8
							12	-12
LVCMOS 1.2	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-2
							8	-6
							0.1	-0.1
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
PCI	-0.3	$0.3V_{CCIO}$	$0.5V_{CCIO}$	3.6	$0.1V_{CCIO}$	$0.9V_{CCIO}$	1.5	-0.5
SSTL25 Class I	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	0.54	$V_{CCIO} - 0.62$	8	8
SSTL25 Class II	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	NA	NA	NA	NA
SSTL18 Class I	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	0.40	$V_{CCIO} - 0.40$	8	8
SSTL18 Class II	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	NA	NA	NA	NA
HSTL18 Class I	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	$V_{CCIO} - 0.40$	8	8
HSTL18 Class II	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS25R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS18R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS18R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS15R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS15R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS12R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain

LVDS Emulation

MachXO2 devices can support LVDS outputs via emulation (LVDS25E). The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

Figure 3-1. LVDS Using External Resistors (LVDS25E)

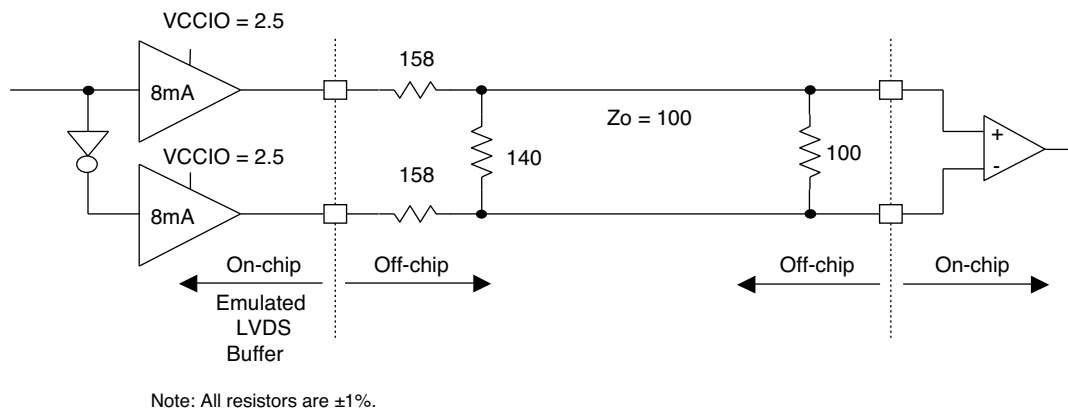


Table 3-1. LVDS25E DC Conditions

Over Recommended Operating Conditions

Parameter	Description	Typ.	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	158	Ohms
R_P	Driver parallel resistor	140	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.43	V
V_{OL}	Output low voltage	1.07	V
V_{OD}	Output differential voltage	0.35	V
V_{CM}	Output common mode voltage	1.25	V
Z_{BACK}	Back impedance	100.5	Ohms
I_{DC}	DC output current	6.03	mA

RSDS

The MachXO2 family supports the differential RSDS standard. The output standard is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all the devices. The RSDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-4 is one possible solution for RSDS standard implementation. Use LVDS25E mode with suggested resistors for RSDS operation. Resistor values in Figure 3-4 are industry standard values for 1% resistors.

Figure 3-4. RSDS (Reduced Swing Differential Standard)

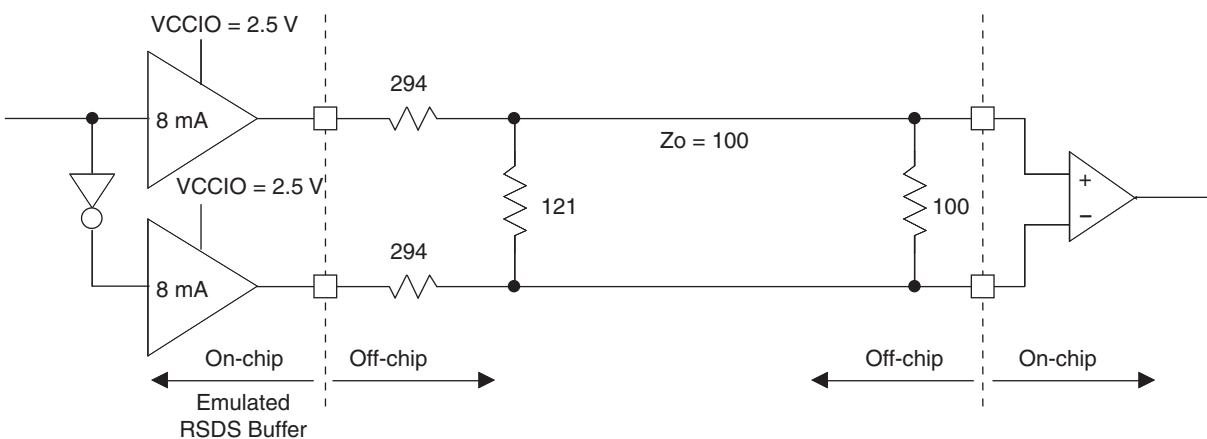


Table 3-4. RSDS DC Conditions

Parameter	Description	Typical	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	294	Ohms
R_P	Driver parallel resistor	121	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.35	V
V_{OL}	Output low voltage	1.15	V
V_{OD}	Output differential voltage	0.20	V
V_{CM}	Output common mode voltage	1.25	V
Z_{BACK}	Back impedance	101.5	Ohms
I_{DC}	DC output current	3.66	mA

Typical Building Block Function Performance – HC/HE Devices¹

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)

Function	-6 Timing	Units
Basic Functions		
16-bit decoder	8.9	ns
4:1 MUX	7.5	ns
16:1 MUX	8.3	ns

Register-to-Register Performance

Function	-6 Timing	Units
Basic Functions		
16:1 MUX	412	MHz
16-bit adder	297	MHz
16-bit counter	324	MHz
64-bit counter	161	MHz
Embedded Memory Functions		
1024x9 True-Dual Port RAM (Write Through or Normal, EBR output registers)	183	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (one PFU)	500	MHz

1. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.

Figure 3-5. Receiver RX.CLK.Aligned and MEM DDR Input Waveforms

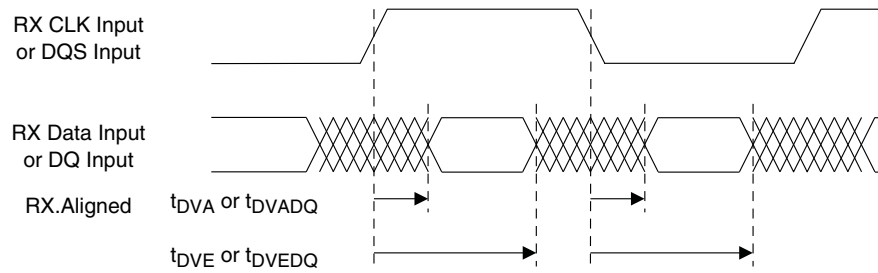


Figure 3-6. Receiver RX.CLK.Centered Waveforms

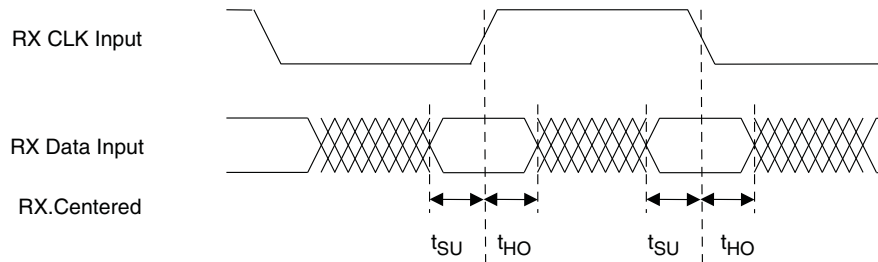


Figure 3-7. Transmitter TX.CLK.Aligned Waveforms

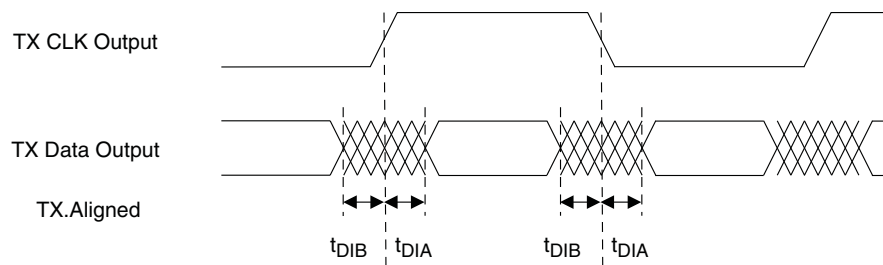
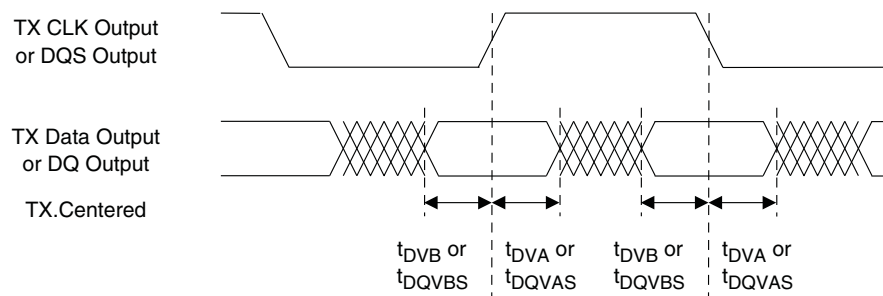


Figure 3-8. Transmitter TX.CLK.Centered and MEM DDR Output Waveforms



sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Min.	Max.	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)		7	400	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS, CLKOS2)		1.5625	400	MHz
f_{OUT2}	Output Frequency (CLKOS3 cascaded from CLKOS2)		0.0122	400	MHz
f_{VCO}	PLL VCO Frequency		200	800	MHz
f_{PFD}	Phase Detector Input Frequency		7	400	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	Without duty trim selected ³	45	55	%
$t_{DT_TRIM}^7$	Edge Duty Trim Accuracy		-75	75	%
t_{PH}^4	Output Phase Accuracy		-6	6	%
$t_{OPJIT}^{1,8}$	Output Clock Period Jitter	$f_{OUT} > 100$ MHz	—	150	ps p-p
		$f_{OUT} < 100$ MHz	—	0.007	UIPP
	Output Clock Cycle-to-cycle Jitter	$f_{OUT} > 100$ MHz	—	180	ps p-p
		$f_{OUT} < 100$ MHz	—	0.009	UIPP
	Output Clock Phase Jitter	$f_{PFD} > 100$ MHz	—	160	ps p-p
		$f_{PFD} < 100$ MHz	—	0.011	UIPP
	Output Clock Period Jitter (Fractional-N)	$f_{OUT} > 100$ MHz	—	230	ps p-p
		$f_{OUT} < 100$ MHz	—	0.12	UIPP
	Output Clock Cycle-to-cycle Jitter (Fractional-N)	$f_{OUT} > 100$ MHz	—	230	ps p-p
		$f_{OUT} < 100$ MHz	—	0.12	UIPP
t_{SPO}	Static Phase Offset	Divider ratio = integer	-120	120	ps
t_W	Output Clock Pulse Width	At 90% or 10% ³	0.9	—	ns
$t_{LOCK}^{2,5}$	PLL Lock-in Time		—	15	ms
t_{UNLOCK}	PLL Unlock Time		—	50	ns
t_{IPJIT}^6	Input Clock Period Jitter	$f_{PFD} \geq 20$ MHz	—	1,000	ps p-p
		$f_{PFD} < 20$ MHz	—	0.02	UIPP
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{STABLE}^5	STANDBY High to PLL Stable		—	15	ms
t_{RST}	RST/RESETM Pulse Width		1	—	ns
t_{RSTREC}	RST Recovery Time		1	—	ns
t_{RST_DIV}	RESETC/D Pulse Width		10	—	ns
t_{RSTREC_DIV}	RESETC/D Recovery Time		1	—	ns
$t_{ROTATE-SETUP}$	PHASESTEP Setup Time		10	—	ns

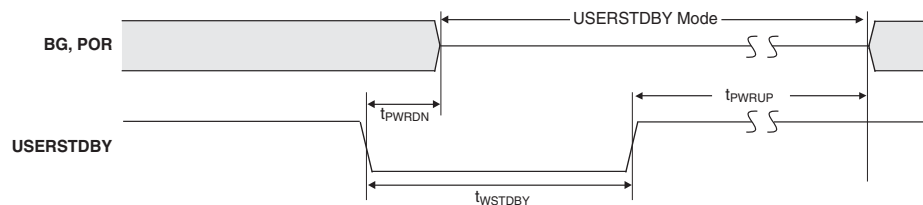
MachXO2 Oscillator Output Frequency

Symbol	Parameter	Min.	Typ.	Max	Units
f_{MAX}	Oscillator Output Frequency (Commercial Grade Devices, 0 to 85°C)	125.685	133	140.315	MHz
	Oscillator Output Frequency (Industrial Grade Devices, -40 °C to 100 °C)	124.355	133	141.645	MHz
t_{DT}	Output Clock Duty Cycle	43	50	57	%
t_{OPJIT}^1	Output Clock Period Jitter	0.01	0.012	0.02	UIPP
$t_{STABLEOSC}$	STDBY Low to Oscillator Stable	0.01	0.05	0.1	μs

1. Output Clock Period Jitter specified at 133 MHz. The values for lower frequencies will be smaller UIPP. The typical value for 133 MHz is 95 ps and for 2.08 MHz the typical value is 1.54 ns.

MachXO2 Standby Mode Timing – HC/HE Devices

Symbol	Parameter	Device	Min.	Typ.	Max	Units
t_{PWRDN}	USERSTDBY High to Stop	All	—	—	9	ns
t_{PWRUP}	USERSTDBY Low to Power Up	LCMXO2-256		—		μs
		LCMXO2-640		—		μs
		LCMXO2-640U		—		μs
		LCMXO2-1200	20	—	50	μs
		LCMXO2-1200U		—		μs
		LCMXO2-2000		—		μs
		LCMXO2-2000U		—		μs
		LCMXO2-4000		—		μs
		LCMXO2-7000		—		μs
t_{WSTDBY}	USERSTDBY Pulse Width	All	18	—	—	ns



MachXO2 Standby Mode Timing – ZE Devices

Symbol	Parameter	Device	Min.	Typ.	Max	Units
t_{PWRDN}	USERSTDBY High to Stop	All	—	—	13	ns
t_{PWRUP}	USERSTDBY Low to Power Up	LCMXO2-256		—		μs
		LCMXO2-640		—		μs
		LCMXO2-1200	20	—	50	μs
		LCMXO2-2000		—		μs
		LCMXO2-4000		—		μs
		LCMXO2-7000		—		μs
t_{WSTDBY}	USERSTDBY Pulse Width	All	19	—	—	ns
$t_{BNDGAPSTBL}$	USERSTDBY High to Bandgap Stable	All	—	—	15	ns

Flash Download Time^{1, 2}

Symbol	Parameter	Device	Typ.	Units
t_{REFRESH}	POR to Device I/O Active	LCMXO2-256	0.6	ms
		LCMXO2-640	1.0	ms
		LCMXO2-640U	1.9	ms
		LCMXO2-1200	1.9	ms
		LCMXO2-1200U	1.4	ms
		LCMXO2-2000	1.4	ms
		LCMXO2-2000U	2.4	ms
		LCMXO2-4000	2.4	ms
		LCMXO2-7000	3.8	ms

1. Assumes sysMEM EBR initialized to an all zero pattern if they are used.

2. The Flash download time is measured starting from the maximum voltage of POR trip point.

JTAG Port Timing Specifications

Symbol	Parameter	Min.	Max.	Units
f_{MAX}	TCK clock frequency	—	25	MHz
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	10	—	ns
t_{BTH}	TCK [BSCAN] hold time	8	—	ns
t_{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
t_{BTCODIS}	TAP controller falling edge of clock to valid disable	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	20	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
t_{BTUODIS}	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
t_{BTUPOEN}	BSCAN test update register, falling edge of clock to valid enable	—	25	ns



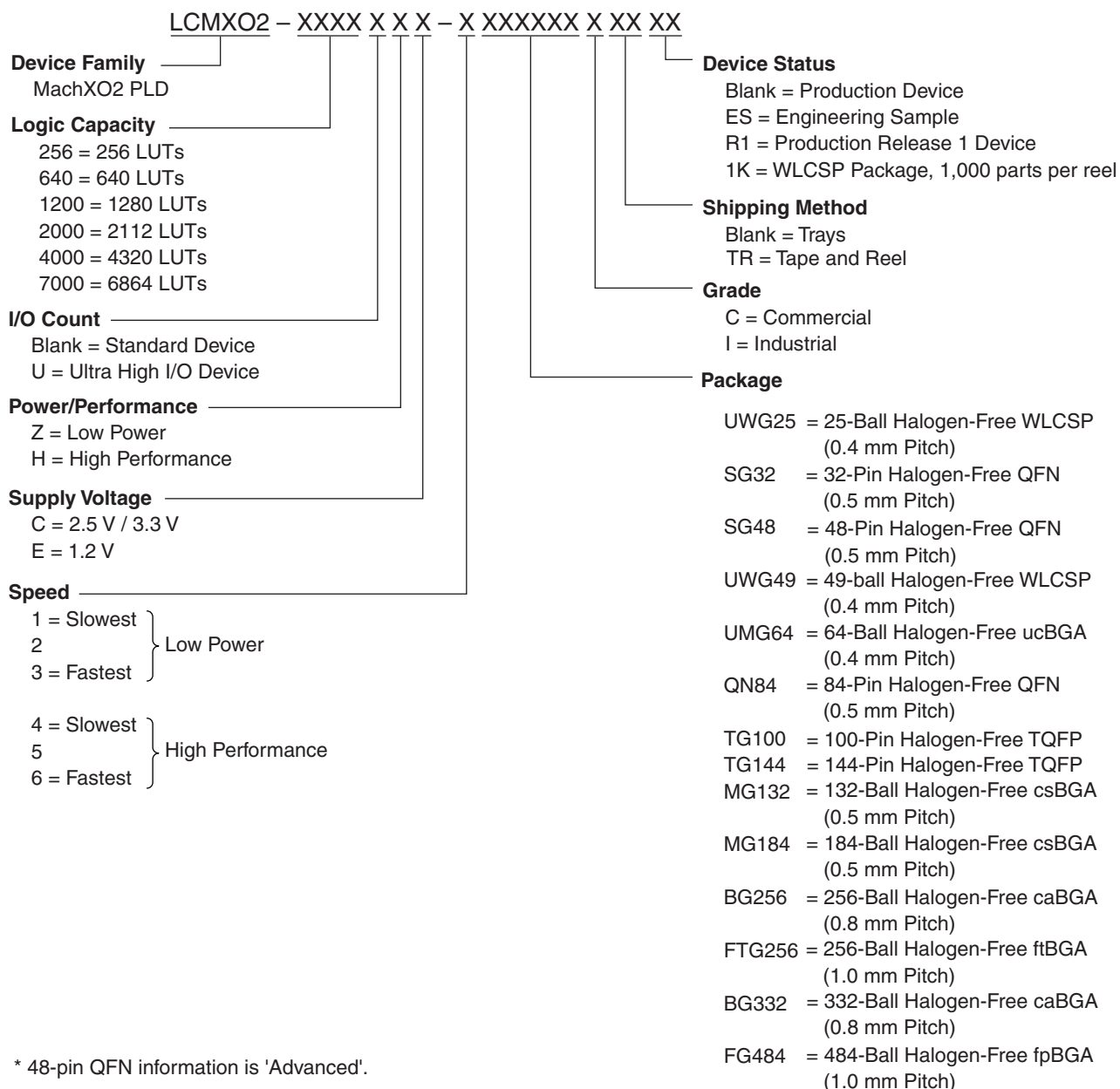
MachXO2 Family Data Sheet

Ordering Information

March 2017

Data Sheet DS1035

MachXO2 Part Number Description



Ultra Low Power Commercial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-256ZE-1SG32C	256	1.2 V	–1	Halogen-Free QFN	32	COM
LCMXO2-256ZE-2SG32C	256	1.2 V	–2	Halogen-Free QFN	32	COM
LCMXO2-256ZE-3SG32C	256	1.2 V	–3	Halogen-Free QFN	32	COM
LCMXO2-256ZE-1UMG64C	256	1.2 V	–1	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-2UMG64C	256	1.2 V	–2	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-3UMG64C	256	1.2 V	–3	Halogen-Free ucBGA	64	COM
LCMXO2-256ZE-1TG100C	256	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-2TG100C	256	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-3TG100C	256	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-256ZE-1MG132C	256	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-256ZE-2MG132C	256	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-256ZE-3MG132C	256	1.2 V	–3	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640ZE-1TG100C	640	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-2TG100C	640	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-3TG100C	640	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-640ZE-1MG132C	640	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-640ZE-2MG132C	640	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-640ZE-3MG132C	640	1.2 V	–3	Halogen-Free csBGA	132	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1SG32C	1280	1.2 V	–1	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-2SG32C	1280	1.2 V	–2	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-3SG32C	1280	1.2 V	–3	Halogen-Free QFN	32	COM
LCMXO2-1200ZE-1TG100C	1280	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-2TG100C	1280	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-3TG100C	1280	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-1MG132C	1280	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-2MG132C	1280	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-3MG132C	1280	1.2 V	–3	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-1TG144C	1280	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-2TG144C	1280	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-3TG144C	1280	1.2 V	–3	Halogen-Free TQFP	144	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200HC-4TG100IR1 ¹	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-5TG100IR1 ¹	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-6TG100IR1 ¹	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-4MG132IR1 ¹	1280	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-5MG132IR1 ¹	1280	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-6MG132IR1 ¹	1280	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-4TG144IR1 ¹	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-1200HC-5TG144IR1 ¹	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-1200HC-6TG144IR1 ¹	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	IND

1. Specifications for the “LCMXO2-1200HC-speed package IR1” are the same as the “LCMXO2-1200ZE-speed package I” devices respectively, except as specified in the [R1 Device Specifications](#) section of this data sheet.

Date	Version	Section	Change Summary
May 2016	3.2	All	Moved designation for 84 QFN package information from 'Advanced' to 'Final'.
		Introduction	Updated the Features section. Revised Table 1-1, MachXO2 Family Selection Guide. — Added 'Advanced' 48 QFN package. — Revised footnote 6. — Added footnote 9.
		DC and Switching Characteristics	Updated the MachXO2 External Switching Characteristics – HC/HE Devices section. Added footnote 12.
			Updated the MachXO2 External Switching Characteristics – ZE Devices section. Added footnote 12.
		Pinout Information	Updated the Signal Descriptions section. Added information on GND signal.
			Updated the Pinout Information Summary section. — Added 'Advanced' MachXO2-256 48 QFN values. — Added 'Advanced' MachXO2-640 48 QFN values. — Added footnote to GND. — Added footnotes 2 and 3.
		Ordering Information	Updated the MachXO2 Part Number Description section. Added 'Advanced' SG48 package and revised footnote.
Updated the Ordering Information section. — Added part numbers for 'Advanced' QFN 48 package.			
March 2016	3.1	Introduction	Updated the Features section. Revised Table 1-1, MachXO2 Family Selection Guide. — Added 32 QFN value for XO2-1200. — Added 84 QFN (7 mm x 7 mm, 0.5 mm) package. — Modified package name to 100-pin TQFP. — Modified package name to 144-pin TQFP. — Added footnote.
		Architecture	Updated the Typical I/O Behavior During Power-up section. Removed reference to TN1202.
		DC and Switching Characteristics	Updated the sysCONFIG Port Timing Specifications section. Revised t _{DPPDONE} and t _{DPPINIT} Max. values per PCN 03A-16, released March 2016.
		Pinout Information	Updated the Pinout Information Summary section. — Added MachXO2-1200 32 QFN values. — Added 'Advanced' MachXO2-4000 84 QFN values.
		Ordering Information	Updated the MachXO2 Part Number Description section. Added 'Advanced' QN84 package and footnote.
			Updated the Ordering Information section. — Added part numbers for 1280 LUTs QFN 32 package. — Added part numbers for 4320 LUTs QFN 84 package.
		March 2015	3.0
Architecture	Updated the Device Configuration section. Added JTAGENB to TAP dual purpose pins.		